

Attorney Reference: 123037-05029639
Preliminary Amendment
Page 3

Amendment to the Abstract of the Disclosure:

Please insert the Abstract of the Disclosure from the International application as attached on the separate sheet herewith.

ABSTRACT OF THE DISCLOSURE

In a process for manufacturing a hyperfine semiconductor device, an apparatus for manufacturing a semiconductor device such as a schottky barrier MOSFET and a method for manufacturing the semiconductor device using the same are provided. Two chambers are connected with each other. A cleaning process, a metal layer forming process, and subsequent processes can be performed in situ by using the two chambers, thereby the attachment of the unnecessary impurities and the formation of the oxide can be prevented and the optimization of the process can be accomplished.